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- A-Suffix Versions Offer 5-mV VIO
- B-Suffix Versions Offer 2-mV VIO
- Wide Range of Supply Voltages 1.4 V to 16 V
- **True Single-Supply Operation**
- Common-Mode Input Voltage Includes the **Negative Rail**
- Low Noise . . . 25 nV/ \sqrt{Hz} Typ at f = 1 kHz (High-Bias Version)

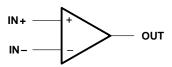
(TOP VIEW) 10UT [14 1 40UT 1IN-[] 2 13 4IN-1IN+[] 3 12 ¶ 4IN+ V_{DD} [] 4 11 V_{DD}_/GND 2IN+ [] 5 10 3IN+ 2IN- **1** 6 9**∏** 2IN− 20UT [8 3OUT

D. N. OR PW PACKAGE

description

The TLC254, TLC254A, TLC254B, TLC25L4, TLC254L4A, TLC254L4B, TLC25M4, TLC25M4A and TL25M4B are low-cost, low-power quad operational amplifiers designed to operate with single or dual supplies. These devices utilize the Texas Instruments silicon gate LinCMOS™

symbol (each amplifier)



process, giving them stable input-offset voltages that are available in selected grades of 2, 5, or 10 mV maximum, very high input impedances, and extremely low input offset and bias currents. Because the input common-mode range extends to the negative rail and the power consumption is extremely low, this series is ideally suited for battery-powered or energy-conserving applications. The series offers operation down to a 1.4-V supply, is stable at unity gain, and has excellent noise characteristics.

These devices have internal electrostatic-discharge (ESD) protection circuits that prevent catastrophic failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.1. However, care should be exercised in handling these devices as exposure to ESD may result in degradation of the device parametric performance.

Because of the extremely high input impedance and low input bias and offset currents, applications for these devices include many areas that have previously been limited to BIFET and NFET product types. Any circuit using high-impedance elements and requiring small offset errors is a good candidate for cost-effective use of these devices. Many features associated with bipolar technology are available with LinCMOS operational amplifiers without the power penalties of traditional bipolar devices.

Available options

	Viemay	PAC	KAGED DEVICES		CHIP FORM
TA	V _{IO} max AT 25°C	SMALL OUTLINE PLASTIC DIP (N)		TSSOP (PW)	(Y)
	10 mV	TLC254CD	TLC254CN	TLC254CPW	TLC254Y
	5 mV	TLC254ACD	TLC254ACN	—	—
	2 mV	TLC254BCD	TLC254BCN	—	—
0°C to 70°C	10 mV	TLC25L4CD	TLC25L4CN	TLC25L4CPW	TLC25L4Y
	5 mV	TLC25L4ACD	TLC25L4ACN	—	—
	2 mV	TLC25L2BCD	TLC25L4BCN	—	—
	10 mV	TLC25M4CD	TLC25M4CN	TLC25M4CPW	TLC25M4Y
	5 mV	TLC25M4ACD	TLC25M4ACN	—	—
	2 mV	TLC25M4BCD	TLC25M4BCN	—	—

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLC254CDR). Chips are tested at 25°C.

LinCMOS is a trademark of Texas Instruments.



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description (continued)

General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are all easily designed with these devices. Remote and inaccessible equipment applications are possible using their low-voltage and low-power capabilities. These devices are well suited to solve the difficult problems associated with single-battery and solar-cell-powered applications. This series includes devices that are characterized for the commercial temperature range and are available in 14-pin plastic dip and the small-outline packages. The device is also available in chip form.

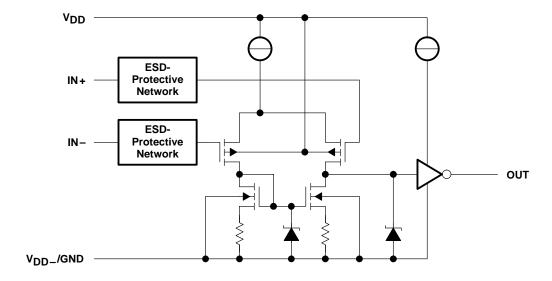
These devices are characterized for operation from 0°C to 70°C.

DEVICE FEATURES

PARAMETER	TLC25L4_C (LOW BIAS)	TLC25M4_C (MEDIUM BIAS)	TLC254_C (HIGH BIAS)
Supply current (Typ)	40 μΑ	600 μΑ	4000 μΑ
Slew rate (Typ)	0.04 V/μA	0.6 V/μA	4.5 V/μA
Input offset voltage (Max) TLC254C, TLC25L4C, TLC25M4C TLC254AC, TLC25L4AC, TLC25M4AC TLC254BC, TLC25L4BC, TLC25M4BC	10 mV 5 mV 2 mV	10 mV 5 mV 2 mV	10 mV 5 mV 2 mV
Offset voltage drift (Typ)	0.1 μV/month [†]	0.1 μV/month [†]	0.1 μV/month [†]
Offset voltage temperature coefficient (Typ)	0.7 μV/°C	2 μV/°C	5 μV/°C
Input bias current (Typ)	1 pA	1 pA	1 pA
Input offset current (Typ)	1 pA	1 pA	1 pA

[†] The long-term drift value applies after the first month.

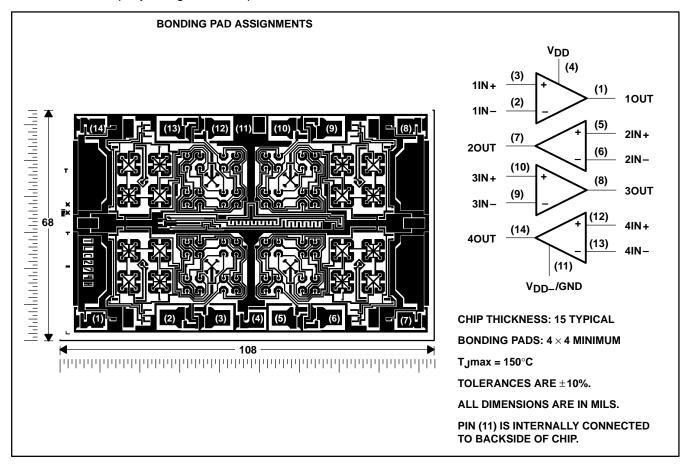
equivalent schematic (each amplifier)



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chip information

These chips, when properly assembled, display characteristics similar to the TLC25_4C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage (see Note 2)	±18 V
Input voltage range (any input)	0.3 V to 18 V
Duration of short-circuit at (or below) 25°C free-air temperature (see Note 3)	unlimited
Continuous total dissipation	. See Dissipation Rating Table
Operating free-air temperature range	0°C to 70°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD}_/GND.
 - 2. Differential voltages are at IN+, with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
N	1050 mW	9.2 mW/°C	736 mW
PW	700 mW	5.6 mW/°C	448 mW

recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V _{DD}		1.4	16	V
	_{DD} = 1.4 V	0	0.2	
Common mode input valtage V/-	/ _{DD} = 5 V	-0.2	4	V
Common-mode input voltage, V _{IC}	_{DD} = 10 V	-0.2	9	V
	_{DD} = 16 V	-0.2	14	
Operating free-air temperature, TA		0	70	°C



electrical characteristics at specified free-air temperature, $V_{DD} = 1.4 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEGT CONDITIONST		TL	.C254_C	;	TL	C25L4_	С	TLO	C25M4_	С	UNIT
	PARAMETER		TEST CONDITIONS†	TA	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
		TLC25_4C		25°C			10			10			10	
		12023_40		0°C to 70°C			12			12			12	
1,40	Input offset voltage	TLC25_4AC	$V_0 = 0.2 \text{ V}, R_S = 50 \Omega$	25°C			5			5			5	mV
VIO	input onset voltage	TLO25_4AC	VO = 0.2 V, NS = 30.22	0°C to 70°C			6.5			6.5			6.5	IIIV
		TLC25_4BC		25°C			2			2			2	
		1LC23_4BC		0°C to 70°C			3			3			3	
a _{VIO}	Average temperature of input offset voltage	coefficient of		25°C to 70°C		1			1			1		μV/°C
1	land effect compact		V- 00V	25°C		1	60		1	60		1	60	A
lio	Input offset current		V _O = 0.2 V	0°C to 70°C			300			300			300	pΑ
1	Innut high current		V- 02V	25°C		1	60		1	60		1	60	~ ^
lΒ	Input bias current		V _O = 0.2 V	0°C to 70°C			600			600			600	pΑ
VICR	Common-mode input v	oltage range		25°C	0 to 0.2			0 to 0.2			0 to 0.2			V
Vом	Peak output voltage sv	ving [‡]	V _{ID} = 100 mV	25°C	450	700		450	700		450	700		mV
A _{VD}	Large-signal differentia	al voltage	$V_O = 100 \text{ to } 300 \text{ mV},$ $R_S = 50 \Omega$	25°C		10			20			20		V/mV
CMRR	Common-mode rejecti	on ratio	$V_O = 0.2 \text{ V},$ $V_{IC} = V_{ICR} \text{min}$	25°C	60	77		60	77		60	77		dB
I_{DD}	Supply current		$V_O = 0.2 \text{ V}$, No load	25°C		600	750		50	68		400	500	μΑ

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Unless otherwise noted, an output load resistor is connected from the output to ground and has the following value: for low bias, R_L = 1 MΩ, for medium bias R_L = 100 kΩ, and for high bias R_L = 10 kΩ. ‡ The output swings to the potential of V_{DD}_/GND.

operating characteristics, V_{DD} = 1.4 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	TLC254_C			TLC25L4_C			TLC25M4_C			UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	See Figure 1		0.1			0.001			0.01		V/μs
В1	Unity-gain bandwidth	$A_V = 40 \text{ dB},$ $C_L = 10 \text{ pF},$ $R_S = 50 \Omega,$ See Figure 1		12			12			12		kHz
	Overshoot factor	See Figure 1		30%			35%			35%		

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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	τ _A †		4, TLC25 .C254B0		UNIT
						MIN	TYP	MAX	
		TLC254C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1102340	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			12	
VIO	Input offset voltage	TLC254AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
VIO	input onset voltage	TLOZDANO	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			6.5	IIIV
		TLC254BC	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.34	2	
		TLC254BC	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			3	
ανιο	Average temperature coeffici offset voltage	ent of input			25°C to 70°C		1.8		μV/°C
l. a	Innut offeet gurrent (e.g. Note	4)	V- 25V	\\\:- 2.5.\\	25°C		0.1	60	m A
lio	Input offset current (see Note	4)	$V_0 = 2.5 V$,	V _{IC} = 2.5 V	70°C		7	300	pΑ
1	Input high current (age Note	()	V _O = 2.5 V,	V _{IC} = 2.5 V	25°C		0.6	60	~ ^
ΙΒ	Input bias current (see Note	+)	V() = 2.5 V,	VIC = 2.5 V	70°C		40	600	pА
	Common-mode input voltage	range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	VICR (see Note 5)				Full range	-0.2 to 3.5			V
					0°C	3	3.8		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	25°C	3.2	3.8		V
					70°C	3	3.8		
					0°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	25°C		0	50	mV
					70°C		0	50	
					0°C	4	27		
A _{VD}	Large-signal differential volta amplification	ge	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 10 \text{ k}\Omega$	25°C	5	23		V/mV
	ampimodion				70°C	4	20		
					0°C	60	84		
CMRR	Common-mode rejection ratio)	$V_{IC} = V_{ICR}$ min		25°C	65	80		dB
					70°C	60	85		
					0°C	60	94		
ksvr	Supply-voltage rejection ratio	(ΔV _{DD} /ΔV _{IO})	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	25°C	65	95		dB
					70°C	60	96		
			V _O = 2.5 V,	V _{IC} = 2.5 V,	0°C		3.1	7.2	
I_{DD}	Supply current (four amplifier	s)	VO = 2.5 V, No load	v IC = 2.5 v,	25°C		2.7	6.4	mA
					70°C		2.3	5.2	

† Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †		C, TLC2 C254B0		UNIT
		_				MIN	TYP	MAX	
		TLC254C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		1102340	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			12	
VIO	Input offset voltage	TLC254AC	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.9	5	mV
1 10	input onset voltage	TLOZJ4AO	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			6.5	IIIV
		TLC254BC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		0.39	2	
		12023400	$R_S = 50 \Omega$,	$R_L = 10 \text{ k}\Omega$	Full range			3	
∝VIO	Average temperature coeffi offset voltage	cient of input			25°C to 70°C		2		μV/°C
	hand effect some of fee a Ne	(- A)	V 5 V		25°C		0.1	60	A
10	Input offset current (see No	te 4)	$V_O = 5 V$	$V_{IC} = 5 V$	70°C		7	300	pΑ
	leaved his a second of the New	- A)	V 5 V		25°C		0.7	60	A
ΙΒ	Input bias current (see Note	9 4)	V _O = 5 V,	$V_{IC} = 5 V$	70°C		50	600	pΑ
	Common mode input volta	no rango			25°C	-0.2 to 9	-0.3 to 9.2		
VICR	VICR Common-mode input voltage range (see Note 5)				Full range	-0.2 to 8.5			V
					0°C	7.8	8.5		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 10 \text{ k}\Omega$	25°C	8	8.5		V
					70°C	7.8	8.4		
					0°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	25°C		0	50	mV
					70°C		0	50	
	l anno aineal differential cal	.			0°C	7.5	42		
AVD	Large-signal differential voluments amplification	tage	$V_0 = 1 V \text{ to } 6 V$,	$R_L = 10 \text{ k}\Omega$	25°C	10	36		V/mV
	ampimodion				70°C	7.5	32		
					0°C	60	88		
CMRR	Common-mode rejection ra	tio	V _{IC} = V _{ICR} min		25°C	65	85		dB
					70°C	60	88		
	Cupply voltogo rojection and	io			0°C	60	94		
ksvr	Supply-voltage rejection rat (ΔVDD/ΔVIO)	liU	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	25°C	65	95		dB
	· · · · · · · · · · · · · · · · · · ·				70°C	60	96		
			V _O = 5 V,	V _{IC} = 5 V,	0°C		4.5	8.8	
IDD	Supply current (four amplifi	ers)	No load	VIC = 5 V,	25°C		3.8	8	mA
					70°C		3.2	6.8	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	т	EST CONDITIO	NS	TA	TLC254	C, TLC2 C254B0		UNIT
							TYP	MAX	
				V _{I(PP)} = 1 V	0°C		4		
				VI(PP) = 1 V	25°C		3.6		
SR	Slew rate at unity gain	$R_L = 10 \text{ k}\Omega$,	C _L = 20 pF,	V _{I(PP)} = 1 V	70°C		3		V/μs
J SIX	Siew rate at unity gain	See Figure 1			0°C		3.1		ν/μ5
				$V_{I(PP)} = 2.5 \text{ V}$	25°C	2.9			
					70°C		2.5		
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		25		nV/√ Hz
				_	0°C		340		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1	$C_L = 20 \text{ pF},$	$R_L = 10 \text{ k}\Omega$,	25°C		320	kHz	
		See Figure 1			70°C		260		
					0°C		2		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 1	25°C		1.7		MHz
					70°C		1.3		
		V 40 V	. 5	0 00 5	0°C		47°		
φm	Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 pF$,	25°C		46°		
	That margin	guio o			70°C		43°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	TE	TEST CONDITIONS			TLC254 TL	C, TLC2 .C254B0		UNIT	
						MIN	TYP	MAX		
					0°C		5.9			
				V _{I(PP)} = 1 V	25°C		5.3			
SR	Slew rate at unity gain	$R_L = 10 \text{ k}\Omega$,			70°C		4.3		V/μs	
Sk Siew rate at unity gain		See Figure 1			0°C		5.1		ν/μ3	
				$V_{I(PP)} = 5.5 V$	25°C		4.6			
					70°C		3.8			
V_n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		25		nV/√ Hz	
			C _L = 20 pF,	_	0°C		220			
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1		$R_L = 10 \text{ k}\Omega,$	25°C		200		kHz	
		Gee rigure r			70°C		140			
					0°C		2.5			
B ₁	Unity-gain bandwidth	$V_I = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 1	25°C		2.2		MHz	
					70°C		1.8			
		V 10 mV	4 D	C. 20 pF	0°C		50°			
φm	Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$	$C_L = 20 \text{ pF},$	25°C		49°			
		1			70°C		46°			

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electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	τ _A †	TL	C25L4C C25L4A C25L4B	С	UNIT
						MIN	TYP	MAX	
		TLC25L4C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		12023240	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	
VIO	Input offset voltage	TLC25L4AC	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		0.9	5	mV
1 10	input onset voltage	TEGZSE4AG	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			6.5	IIIV
		TLC25L4BC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		0.24	2	
		TEG23E4BC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3	
∝VIO	Average temperature coeffi offset voltage	cient of input			25°C to 70°C		1.1		μV/°C
1	land the standard (see No	+- 4\	V- 05V	V 0.5.V	25°C		0.1	60	- ^
li0	Input offset current (see No	te 4)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	70°C		7	300	pΑ
	land this summer (see Net	- 4\	V- 05V	V 0.5.V	25°C		0.6	60	^
IB	Input bias current (see Note	2 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	70°C		40	600	pΑ
V	Common-mode input voltag	ge range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	,			Full range	-0.2 to 3.5			V
					0°C	3	4.1		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	25°C	3.2	4.1		V
					70°C	3	4.2		
					0°C		0	50	
VOL	Low-level output voltage		$V_{1D} = -100 \text{ mV},$	$I_{OL} = 0$	25°C		0	50	mV
					70°C		0	50	
					0°C	50	680		
AVD	Large-signal differential voluments amplification	tage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	25°C	50	520		V/mV
	ampimoation				70°C	50	380		
					0°C	60	95		
CMRR	Common-mode rejection ra	tio	V _{IC} = V _{ICR} min		25°C	65	94		dB
					70°C	60	95		
	Ourantic college and make of the const				0°C	60	97		
ksvr	Supply-voltage rejection rat (ΔV _{DD} /ΔV _{IO})	.IO	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	25°C	70	98		dB
	(DD10)				70°C	60	97		
			V _O = 2.5 V,	V _{IC} = 2.5 V,	0°C		48	84	
lDD	Supply current (four amplifi	ers)	No load	$V_{1C} = 2.5 V_{1}$	25°C		40	68	μΑ
					70°C		31	56	

† Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL	_C25L40 C25L4A C25L4B	С	UNIT
						MIN	TYP	MAX	
		TLC25L4C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		1.1	10	
		12020210	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	
VIO	Input offset voltage	TLC25L4AC	$V_0 = 1.4 V,$	$V_{IC} = 0$,	25°C		0.9	5	mV
1,10	input onoot voltago	120202 17 (0	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			6.5	
		TLC25L4BC	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.26	2	
		120202400	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3	
αVIO	Average temperature coeffi input offset voltage	cient of			25°C to 70°C		1		μV/°C
1	Input offeet gurrent (e.g. No	to 4)	V _O = 5 V,	V:- EV	25°C		0.1	60	π Λ
110	input offset current (see No	offset current (see Note 4)		$V_{IC} = 5 V$	70°C		7	300	pΑ
1	Innut high ourrent (age Note	hine comment (see Note 4)		V:- EV	25°C		0.7	60	- A
ΙΒ	Input bias current (see Note	2 4)	V _O = 5 V,	V _{IC} =.5 V	70°C		50	600	pΑ
	Common mode input valtae	o rango (soo			25°C	-0.2 to	-0.3 to 9.2		V
VICR	Note 5)	mon-mode input voltage range (see 5)			Full range	-0.2 to 8.5			V
					0°C	7.8	8.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	25°C	8	8.9		V
					70°C	7.8	8.9		
					0°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	25°C		0	50	mV
					70°C		0	50	
	Large signal differential val	to a o			0°C	50	1025		
AVD	Large-signal differential volt amplification	lage	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	25°C	50	870		V/mV
					70°C	50	660		
					0°C	60	97		
CMRR	Common-mode rejection ra	tio	VIC = VICRmin		25°C	65	97		dB
					70°C	60	97		
	Cumply voltage rejection and	io			0°C	60	97		
ksvr	Supply-voltage rejection rat (ΔV _{DD} /ΔV _{IO})	10	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	25°C	70	97		dB
	. 55 10/				70°C	60	98		
			V0 - 5 V	V10 - 5 V	0°C		72	132	
IDD	Supply current (four amplific	ers)	$V_O = 5 V$, No load	$V_{IC} = 5 V$	25°C		57	92	μΑ
					70°C		44	80	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



operating characteristics, $V_{DD} = 5 V$

	PARAMETER	TE	ST CONDITION	NS	TA	TLC25L4C TLC25L4AC TLC25L4BC			UNIT
						MIN	TYP	MAX	
					0°C		0.04		
				V _{I(PP)} = 1 V	25°C		0.03		
SR	Slew rate at unity gain	$R_L = 1 M\Omega$,	$C_L = 20 pF$,		70°C		0.03		V/μs
Jok	Siew rate at unity gain	See Figure 1			0°C		0.03		ν/μ5
				$V_{I(PP)} = 2.5 V$	25°C	0.03			
					70°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		70		nV/√ Hz
		., .,			0°C		6		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1	$C_L = 20 pF$,	$R_L = 1 M\Omega$,	25°C		5		kHz
		occ rigare r			70°C		4.5		
					0°C		100		
В1	Unity-gain bandwidth	$V_I = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 1	25°C		85		kHz
					70°C		65		
		\/: 40 m\/	4 D.	C: 20 pF	0°C		36°		
φm	o _m Phase margin	V _I = 10 mV, See Figure 3	$f = B_1$	$C_L = 20 pF$,	25°C		34°		
				70°C		30°			

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	TE	ST CONDITION	ıs	TA	TL TL(С	UNIT		
				_		MIN	TYP	MAX		
					0°C		0.05			
				V _{I(PP)} = 1 V	25°C		0.05			
SR	Slew rate at unity gain	$R_L = 1 M\Omega$, See Figure 1	$C_{L} = 20 pF$,		70°C	0.04			V/μs	
	Siew rate at unity gain				0°C		0.05		ν/μ3	
				$V_{I(PP)} = 5.5 V$	25°C	0.04				
					70°C	0.04				
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		70		nV/√ Hz	
		., .,	0 00 5	D 4140	0°C		1.3			
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1	$C_L = 20 pF$,	$R_L = 1 M\Omega$,	25°C		1		kHz	
		Occ rigure r			70°C		0.9			
					0°C		125			
B ₁	Unity-gain bandwidth	$V_I = 10 \text{ mV},$	$C_{L} = 20 pF$,	See Figure 1	25°C		110		kHz	
					70°C		90			
		\\\. 40>\\	4 D	C 20 = F	0°C		40°			
φm		V _I = 10 mV, See Figure 3		$C_L = 20 pF,$	25°C		38°			
			_	70°C		34°				

electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TLC25M TLC25M4 TLC25M4		C	UNIT
						MIN	TYP	MAX	
		TLC25M4C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLG25W4C	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	
VIO	Input offset voltage	TLC25M4AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	mV
۷IO	input onset voltage	TEGZSIVI4AC	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	1111
		TLC25M4BC	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.25	2	
		TEGZSIVI4BC	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			3	
∝VIO	Average temperature c	oefficient of			25°C to		1.7		μV/°C
*0	input offset voltage		ļ		70°C				
lio	Input offset current (see	ut offset current (see Note 4)		$V_{IC} = 2.5 \text{ V}$	25°C		0.1	60	pА
					70°C 25°C		7	300	·
lв	Input bias current (see	ut bias current (see Note 4)		V _O = 2.5 V, V _{IC} = 2.5 V			0.6	60	pА
		,	ļ -		70°C		40	600	· ·
					25°C	-0.2 t0	-0.3 to		V
	Common-mode input v	oltage range			25 0	4	4.2		V
VICR	(see Note 5)	onage range				-0.2	-		
					Full range	to			V
						3.5			
					0°C	3	3.9		
VOH	High-level output voltag	je	$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	25°C	3.2	3.9		V
					70°C	3	4		
					0°C		0	50	
VOL	Low-level output voltag	е	$V_{ID} = -100 \text{ mV},$	IOT = 0	25°C		0	50	mV
					70°C		0	50	
	Lorgo signal differentia	l volto ao			0°C	15	200		
AVD	Large-signal differentia amplification	voitage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	25°C	25	170		V/mV
	ampimoation				70°C	15	140		
					0°C	60	91		
CMRR	Common-mode rejection	on ratio	V _{IC} = V _{ICR} min		25°C	65	91		dB
					70°C	60	92		
	0 1 1: 1: 1:				0°C	60	92		
kSVR	Supply-voltage rejectio (ΔV _{DD} /ΔV _{IO})	n ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	25°C	70	93		dB
	(A 1 DD A 1 D)				70°C	60	94		
			V 05.V		0°C		500	1280	
I_{DD}	Supply current (four am	plifiers)	$V_O = 2.5 \text{ V},$ No load	$V_{IC} = 2.5 V,$	25°C		420	1120	μΑ
			1.0.000	70°C		340	880		

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST COND	ITIONS	T _A †	TL	.C25M40 C25M4A C25M4B	С	UNIT
		•				MIN	TYP	MAX	
		TLC25M4C	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		1.1	10	
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	
VIO	Input offset voltage	TLC25M4AC	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		0.9	5	mV
'Ŭ	,		$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range	ļ		6.5	
		TLC25M4BC	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		0.26	2	
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3	
αVIO	Average temperature coeffi offset voltage	cient of input			25°C to 70°C		2.1		μV/°C
110	Input offset current (see No	te 4)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.1	60	pА
10	Input onset ourrent (see 140	put onset current (see Note 4)		VIC - 0 V	70°C		7	300	P/ \
I _{IB}	Input hias current (see Note	nput bias current (see Note 4)		V _O = 5 V, V _{IC} = 5 V			0.7	60	pА
, ID	Input blub current (See 140te	out bias current (see Note 4)		VIC - 0 V	70°C		50	600	μ, ,
	Common-mode input voltage range (see				25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	Note 5)	ge range (eee			Full range	-0.2 to 8.5			V
					0°C	7.8	8.7		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV}, R_L = 100 \text{ ks}$		25°C	8	8.7		V
					70°C	7.8	8.7		
					0°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOL = 0	25°C		0	50	mV
					70°C		0	50	
	Lanca d'acadatte				0°C	15	320		
AVD	Large-signal differential volt amplification	age	$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	25°C	25	275		V/mV
	ampilioation				70°C	15	230		
					0°C	60	94		
CMRR	Common-mode rejection ra	tio	$V_{IC} = V_{ICR}min$		25°C	65	94		dB
					70°C	60	94		
					0°C	60	92		-
ksvr	Supply-voltage rejection rati	ο (ΔV _{DD} /ΔV _{IO})	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	25°C	70	93		dB
					70°C	60	94		
			Vo = 5.V	V10 - 5 V	0°C		690	1600	
IDD	Supply current (four amplific	$V_O = 5 V$, V	$V_{IC} = 5 V$,	25°C		570	1200	μΑ	
				70°C		440	1120		

† Full range is 0°C to 70°C.
NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	TE	EST CONDITIO	NS	TA	TLC25M4C TLC25M4AC TLC25M4BC			UNIT
						MIN	TYP	MAX	
				., .,,	0°C		0.46		V/µs
				$V_{I(PP)} = 1 V$	25°C		0.43		V/µs
SR	Slew rate at unity gain	$R_L = 100 \text{ k}\Omega$,	$C_L = 20 pF$,		70°C		0.36		
J SIX	Siew rate at unity gain	See Figure 1			0°C		0.43		V/μs
				$V_{I(PP)} = 2.5 V$	25°C	0.40			ν/μδ
					70°C		0.34		
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		32		nV/√ Hz
		., .,	0 00 5	D 40010	0°C		60		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , See Figure 1	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega,$	25°C		55		kHz
		occ rigare r			70°C		50		
					0°C		610		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	$C_L = 20 pF$,	See Figure 1	25°C		525		kHz
					70°C		400		
		\/: = 10 m\/	f _ D.	C: - 30 pF	0°C		41°		
φm	m Phase margin	$V_I = 10 \text{ mV}, \qquad f = B_1, \qquad C$ See Figure 3		$C_L = 20 \text{ pF},$	25°C		40°		
					70°C		39°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	TE	EST CONDITION	NS	TA	TLC25M4C TLC25M4AC TLC25M4BC			UNIT
				_		MIN	TYP	MAX	
					0°C		0.67		
				$V_{I(PP)} = 1 V$	25°C		0.62		
SR	Slew rate at unity gain	$R_L = 100 \text{ k}\Omega$,	$C_L = 20 pF$,		70°C		0.51	V/μs	
J SIX	Siew rate at unity gain	See Figure 1			0°C		0.61		ν/μ3
				$V_{I(PP)} = 5.5 V$	25°C	0.56			
					70°C		0.46		
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$,	See Figure 2	25°C		32		nV/√ Hz
		., .,			0°C		40		
ВОМ	Maximum output-swing bandwidth	VO = VOH, See Figure 1	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega,$	25°C		35		kHz
		See rigure r			70°C		30		
					0°C		710		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$,	See Figure 1	25°C		635		kHz
					70°C		510		
		V 40 V	, D	0 00 - 5	0°C		44°		
φm		V _I = 10 mV, See Figure 3	$f = B_1$,	$C_L = 20 \text{ pF},$	25°C	°C 43°			
		garo o		70°C		42°			

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electrical characteristics, V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

	DADAMETED	TEST	Т	LC254Y	′	T	LC25L4	Υ	Τι	_C25M4	Υ	UNIT
	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
VIO	Input offset voltage	$V_O = 1.4 \text{ V},$ $V_{IC} = 0 \text{ V},$ $R_S = 50 \Omega,$ See Note 6		1.1	10		1.1	10		1.1	10	mV
ανιο	Average temperature coefficient of input offset voltage			1.8			1.1			1.7		μV/°C
IIO	Input offset current (see Note 4)	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.1	60		0.1	60		0.1	60	pA
I _{IB}	Input bias current (see Note 4)	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.6	60		0.6	60		0.6	60	pA
VICR	Common-mode input voltage range (see Note 5)		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		٧
Vон	High-level output voltage	$V_{ID} = 100 \text{ mV},$ $R_L = 100 \text{ k}\Omega$	3.2	3.8		3.2	4.1		3.2	3.9		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$		0	50		0	50		0	50	mV
A _{VD}	Large-signal differential voltage amplification	V _O = 0.25 V, See Note 6	5	23		50	520		25	170		V/mV
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min	65	80		65	94		65	91		dB
ksvr	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 5 \text{ V to } 10 \text{ V},$ $V_{O} = 1.4 \text{ V}$	65	95		70	97		70	93		dB
I _{DD}	Supply current	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2,$ No load		2.7	6.4		0.04	0.068		0.42	1.12	mA

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

operating characteristics, V_{DD} = 5 V, T_A = 25°C

0	ARAMETER	TEST C	ONDITIONS	Т	LC254Y	,	TI	LC25L4	Υ	TL	.C25M4	Υ	UNIT
P	ARAMETER	l lesi co	SNOTTIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
SR	Slew rate at	C _L = 20 pF,	V _{I(PP)} = 1 V		3.6			0.03			0.43		\//uo
36	unity gain	See Note 6	$V_{I(PP)} = 2.5 V$		2.9			0.03			0.40		V/μs
٧n	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		2.5			70			32		nV/√ Hz
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_L = 10 \text{ k}\Omega$	C _L = 20 pF,		320			5			55		kHz
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		1.7			0.085			0.525		MHz
φm	Phase margin	f = B ₁ , C _L = 20 pF	V _I = 10 mV,		46°			34°			40°		

NOTE 6: For low-bias mode, $R_L = 1 \text{ M}\Omega$, for medium-bias mode, $R_L = 100 \text{ k}\Omega$, and for high-bias mode, $R_L = 10 \text{ k}\Omega$.



^{5.} This range also applies to each input individually.

^{6.} For low-bias mode, R_L = 1 M Ω , for medium-bias mode, R_L = 100 k Ω , and for high-bias mode, R_L = 10 k Ω .

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PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC25_4, TLC25_4A, and TLC25_4B are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

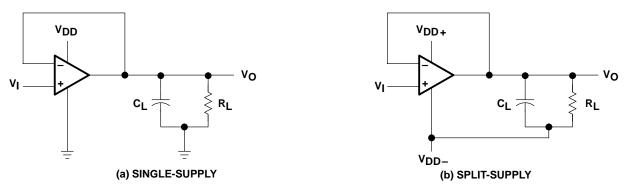


Figure 1. Unity-Gain Amplifier

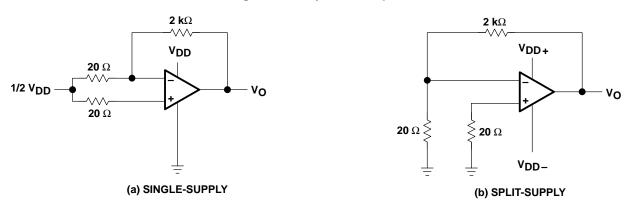


Figure 2. Noise-Test Circuit

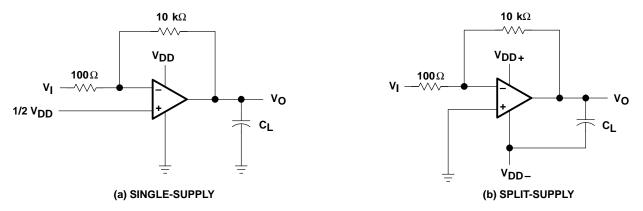


Figure 3. Gain-of-100 Inverting Amplifier



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TYPICAL CHARACTERISTICS

Table of Graphs

				FIGURE
IDD	Supply current		vs Supply voltage vs Free-air temperature	4 5
		Low bias	vs Frequency	6
A_{VD}	Large-signal differential voltage amplification	Medium bias	vs Frequency	7
		High bias	vs Frequency	8
		Low bias	vs Frequency	6
	Phase shift	Medium bias	vs Frequency	7
		High bias	vs Frequency	8

SUPPLY CURRENT VS

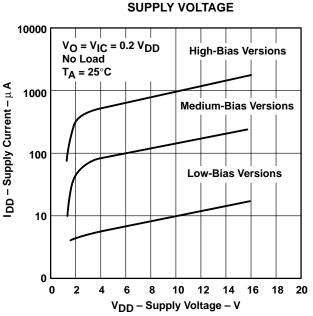


Figure 4

SUPPLY CURRENT vs FREE-AIR TEMPERATURE

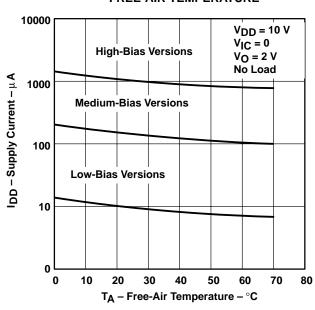


Figure 5

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TYPICAL CHARACTERISTICS

LOW-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

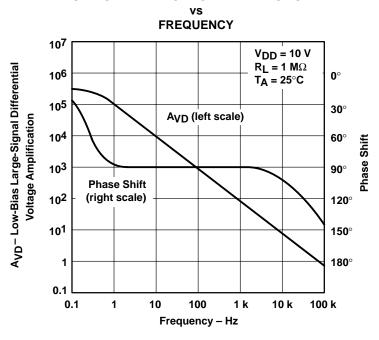


Figure 6

MEDIUM-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

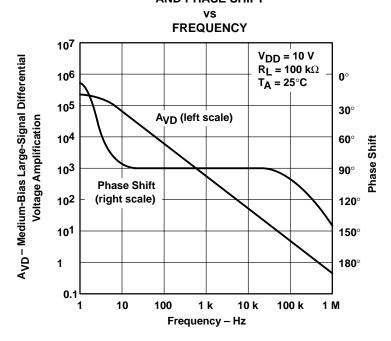


Figure 7



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TYPICAL CHARACTERISTICS

HIGH-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

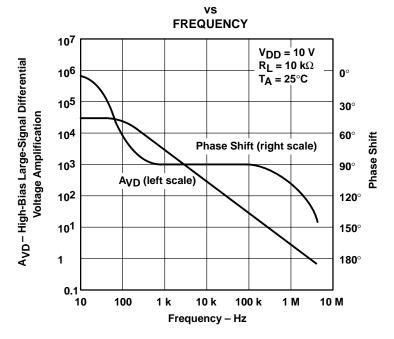


Figure 8

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APPLICATION INFORMATION

latch-up avoidance

Junction-isolated CMOS circuits have an inherent parasitic PNPN structure that can function as an SCR. Under certain conditions, this SCR may be triggered into a low-impedance state, resulting in excessive supply current. To avoid such conditions, no voltage greater than 0.3 V beyond the supply rails should be applied to any pin. In general, the operational amplifiers supplies should be established simultaneously with, or before, application of any input signals.

output stage considerations

The amplifier's output stage consists of a source-follower-connected pullup transistor and an open-drain pulldown transistor. The high-level output voltage (V_{OH}) is virtually independent of the I_{DD} selection and increases with higher values of V_{DD} and reduced output loading. The low-level output voltage (V_{OL}) decreases with reduced output current and higher input common-mode voltage. With no load, V_{OL} is essentially equal to the potential of V_{DD} –/GND.

supply configurations

Even though the TLC25_4C series is are characterized for single-supply operation, they can be used effectively in a split-supply configuration if the input common-mode voltage (V_{ICR}), output swing (V_{OL} and V_{OH}), and supply voltage limits are not exceeded.

circuit layout precautions

Whenever extremely high circuit impedances are used, care must be exercised in layout, construction, board cleanliness, and supply filtering to avoid hum and noise pickup as well as excessive dc leakages.



30-Jul-2011

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC254ACD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC254ACDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC254ACN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC254ACNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC254BCD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC254BCDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC254BCN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC254BCNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC254CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC254CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC254CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC254CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25L4ACN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25L4ACNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25L4BCD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC25L4BCDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC25L4BCN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25L4BCNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25L4CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC25L4CDB	OBSOLETE	SSOP	DB	14		TBD	Call TI	Call TI	
TLC25L4CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC25L4CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	





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Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC25L4CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25M4ACDR	PREVIEW	SOIC	D	14		TBD	Call TI	Call TI	
TLC25M4ACN	OBSOLETE	PDIP	N	14		TBD	Call TI	Call TI	
TLC25M4BCD	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	
TLC25M4BCN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25M4BCNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25M4CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC25M4CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC25M4CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC25M4CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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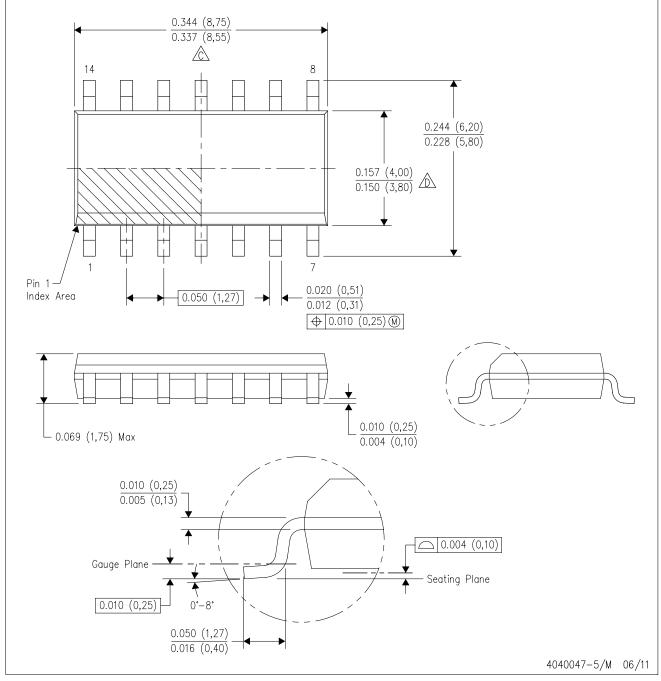
PACKAGE OPTION ADDENDUM

30-Jul-2011

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

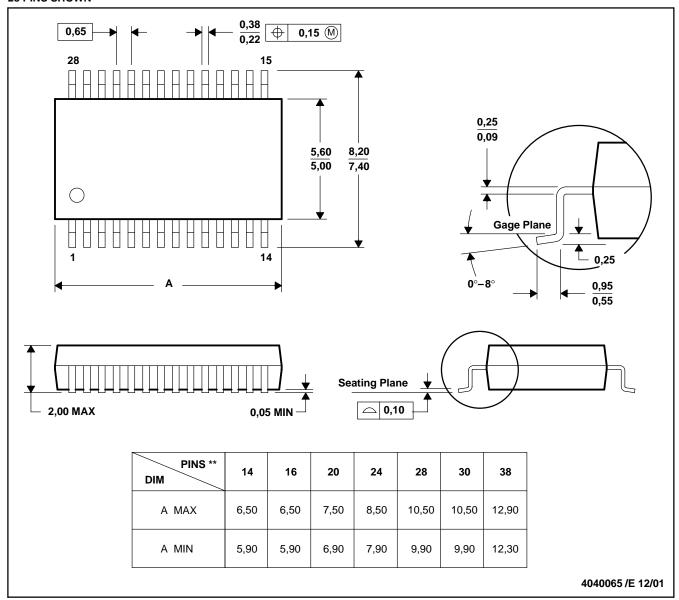
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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